



P-Channel NexFET™ Power MOSFETs

Check for Samples: CSD25401Q3

FEATURES

- Ultra Low Q_q and Q_{qd}
- Low Thermal Resistance
- Low R_{DS(on)}
- · Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3mm x 3.3mm Plastic Package

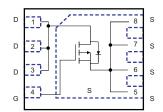
APPLICATIONS

- DC-DC Converters
- Battery Management
- Load Switch
- Battery Protection

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion load management applications. The SON 3×3 package offers excellent thermal performance for the size of the package.





R_{DS(ON)} vs V_{GS}

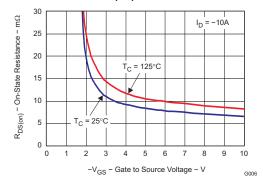


Table 1. PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	-20	V	
Q_g	Gate Charge Total (4.5V)	8.8	nC	
Q_{gd}	Gate Charge Gate to Drain 2.1			nC
D	Drain to Source On Resistance	$V_{GS} = -2.5V$	13.5	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -4.5V$	8.8	mΩ
V_{th}	Threshold Voltage	-0.85	V	

ORDERING INFORMATION

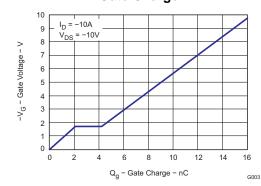
Device Package		Media	Qty	Ship	
CSD25401Q3	SON 3 x 3 Plastic Package	13-inch reel	2500	Tape and Reel	

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	-20	٧
V_{GS}	Gate to Source Voltage	+12 / -12	٧
	Continuous Drain Current, T _C = 25°C	-60	Α
I _D	Continuous Drain Current ⁽¹⁾	-14	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	-82	Α
P_D	Power Dissipation ⁽¹⁾	2.8	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

- (1) $R_{\theta JA} = 45^{\circ}\text{C/W}$ on 1inch² Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%

Gate Charge



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ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics		·			
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V$, $V_{DS} = -20V$ to $-16V$			-1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 12V$			-100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6	-0.85	-1.2	V
	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -10A$		13.5	18.2	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -4.5V, I_D = -10A$		8.8	11.7	mΩ
g _{fs}	Transconductance	$V_{DS} = -15V, I_D = -10A$		43		S
Dynamic	Characteristics		•			
C _{ISS}	Input Capacitance			1070	1400	pF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{DS} = -10V,$ $f = 1MHz$		560	730	pF
C _{RSS}	Reverse Transfer Capacitance	1 - 111112		180	230	pF
Qg	Gate Charge Total (4.5V)			8.8	12.3	nC
Q _{gd}	Gate Charge Gate to Drain	V 40V I 40A		2.1		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = -10V, I_{D} = -10A$		2.1		nC
Q _{g(th)}	Gate Charge at Vth			0.9		nC
Q _{OSS}	Output Charge	$V_{DS} = -10V, V_{GS} = 0V$		8.2		nC
t _{d(on)}	Turn On Delay Time			8.1		ns
t _r	Rise Time	$V_{DS} = -10V, V_{GS} = -4.5V,$		3.9		ns
t _{d(off)}	Turn Off Delay Time	$I_D = -10A$, $R_G = 5.1\Omega$		13.5		ns
t _f	Fall Time			12.6		ns
Diode Cl	haracteristics					
V _{SD}	Diode Forward Voltage	$I_S = -10A$, $V_{GS} = 0V$		-0.7	-1	V
Q _{rr}	Reverse Recovery Charge	$V_{DD} = -12.5V$, $I_F = -10A$,	17.4			nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/µs		21		ns

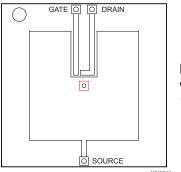
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

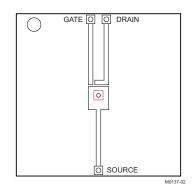
	PARAMETER	MIN	TYP	MAX	UNIT
R _{θJC}	Thermal Resistance Junction to Case ⁽¹⁾ (2)			2.8	°C/W
R _{0JA}	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			57	°C/W

 ⁽¹⁾ R _{θJC} is determined with the device mounted on a 1 inch² Cu (2 oz.) pad on a 1.5 x 1.5 in 0.060 inch thick FR4 board. R _{θJC} is specified by design while R _{θJA} is determined by the user's board design.
 (2) Device mounted on FR4 Material with 1 inch² of Cu (2 oz.).





Max $R_{\theta JA} = 57^{\circ}C/W$ when mounted on 1inch² of 2 oz. Cu.



Max $R_{\theta JA} = 158^{\circ}\text{C/W}$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

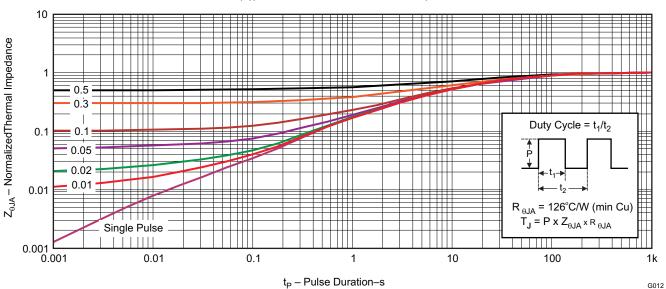


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

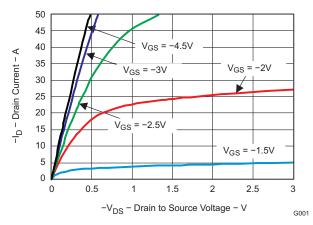


Figure 2. Saturation Characteristics

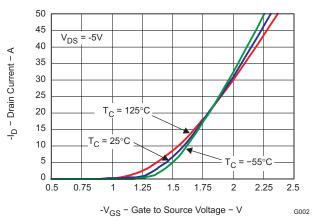


Figure 3. Transfer Characteristics

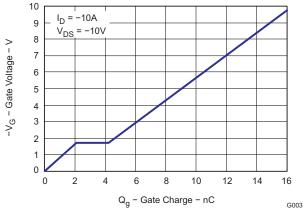


Figure 4. Gate Charge

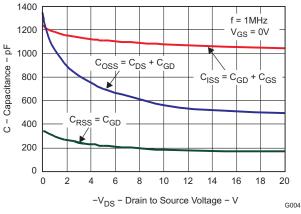


Figure 5. Capacitance

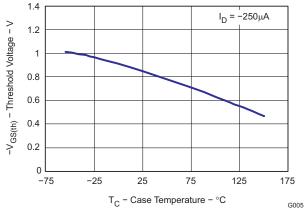


Figure 6. Threshold Voltage vs. Temperature

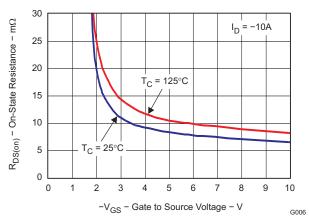


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

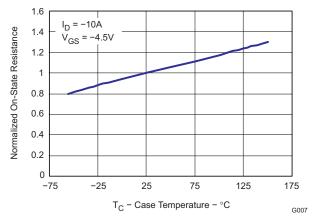


Figure 8. On Resistance vs. Temperature

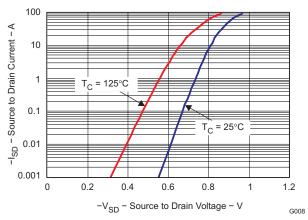


Figure 9. Typical Diode Forward Voltage

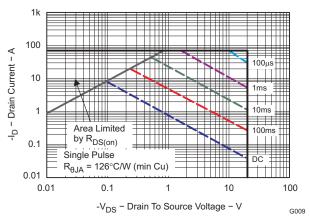


Figure 10. Maximum Safe Operating Area

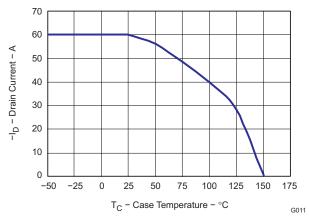
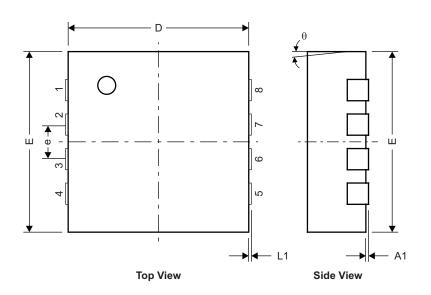


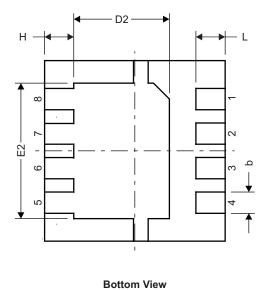
Figure 11. Maximum Drain Current vs. Temperature

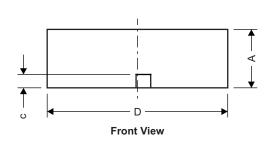


MECHANICAL DATA

CSD25401Q3 Package Dimensions







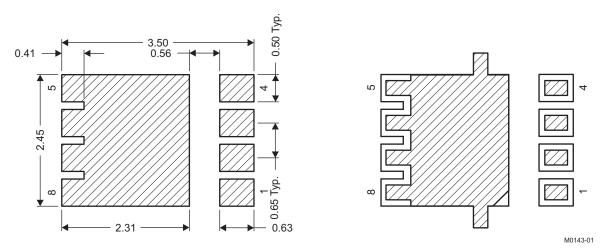
Pinout					
Drain	1,2,3				
Gate	4				
Source	5,6,7,8				

M0142-01

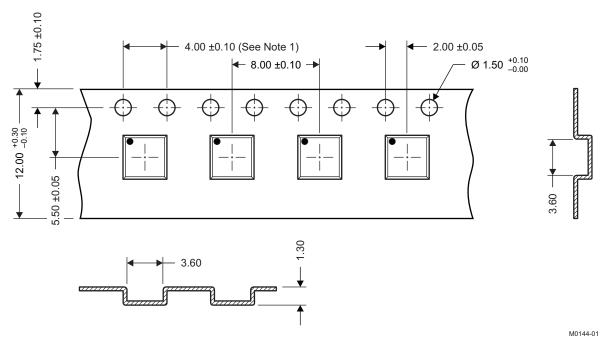
DIM	MILLIMETERS			INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
А	0.950	1.000	1.100	0.037	0.039	0.043	
A1	0.000	0.000	0.050	0.000	0.000	0.002	
b	0.280	0.340	0.400	0.011	0.013	0.016	
С	0.150	0.200	0.250	0.006	0.008	0.010	
D	3.200	3.300	3.400	0.126	0.130	0.134	
D1	_	_	_	_	_	-	
D2	1.650	1.750	1.800	0.065	0.069	0.071	
E	3.200	3.300	3.400	0.126	0.130	0.134	
E1	-	-	-	-	-	_	
E2	2.350	2.450	2.550	0.093	0.096	0.100	
е	e 0.650 TYP				0.026		
Н	0.35	0.450	0.550	0.014	0.018	0.022	
L	0.35	0.450	0.550	0.014	0.018	0.022	
L1	_	_	-	-	-	_	
θ	_	_	_	-	-	_	



Recommended PCB Pattern



Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Conection) PbF Reflow Compatible



REVISION HISTORY

Changes from Original (August 2009) to Revision A	Page
Changed 300s to 300µs in Note 2 of the Abs Max Ratings table	1
Changed Q _g Gate Charge Total (4.5V) - max value From: 2.3 To: 12.3	2
Changes from Revision A (October 2009) to Revision B	Page
Deleted the Package Marking Information section	7

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25401Q3	SON	DQG	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

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*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
I	CSD25401Q3	SON	DQG	8	2500	335.0	335.0	32.0

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